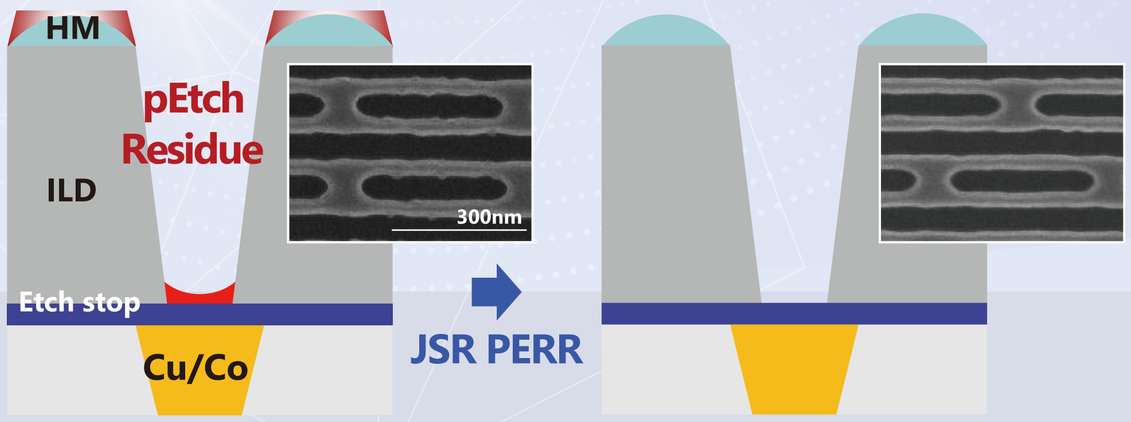
JSR Advanced Wet Chemical

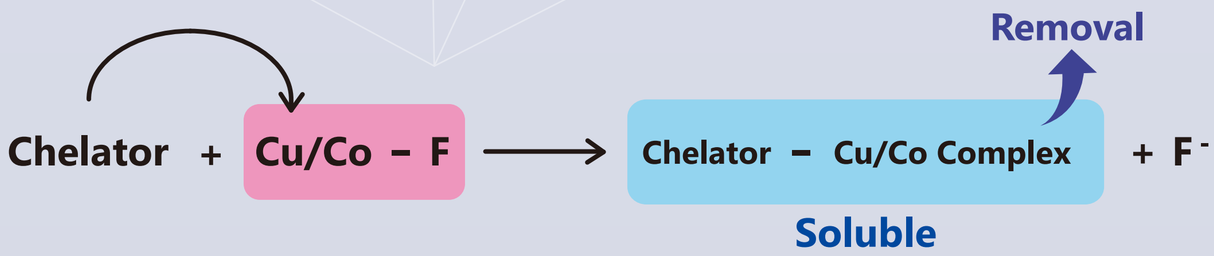
PERR – Cu/Co Clean

PERR: Post-Etch Residue Remover

Balanced etching by combination of Etchant and Chelator

- ✓ The Inhibitor effectively protects Cu and Co surface
- ✓ Etchant selectively removes CF residue and Metal-Ox





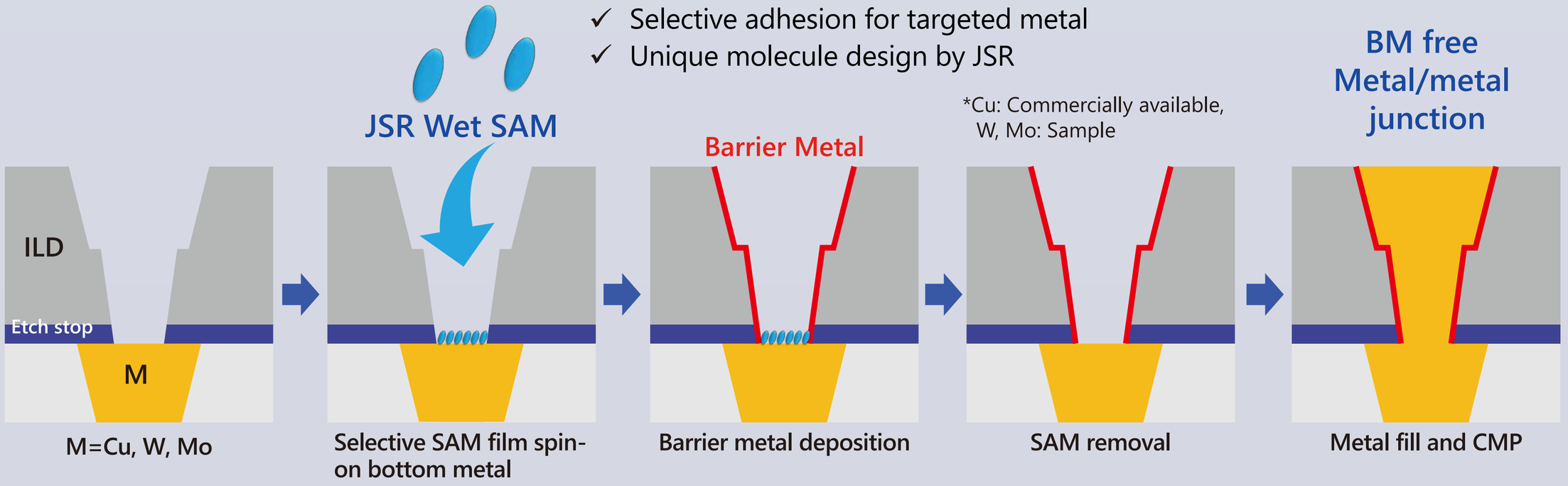
Component		JSR PERR
pH		Neutral
Residue/ AlOx Etchant		Fluoride Etchant
Solvent		<10%
Physical Properties (25℃)	Viscosity	1.1 cP
	Surface tension	30-40 mN/m
Etching behavior	PER	Remove
	Cu	No damage
	Co	
	ILD	
	TEOS	

Wet SAM

SAM: Self-Aligned Monolayer

Selective metal protection by quick wet process

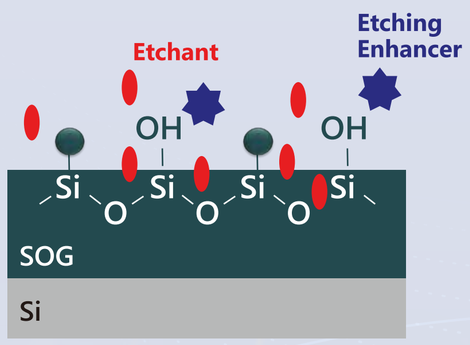
- ✓ Selective adhesion for targeted metal
- ✓ Unique molecule design by JSR



SOG Remover

Selective SOG removal Compatible with other films

- ✓ Etching enhancer weakens Si-O bonding
- ✓ Etchant is absorbed into SOG film

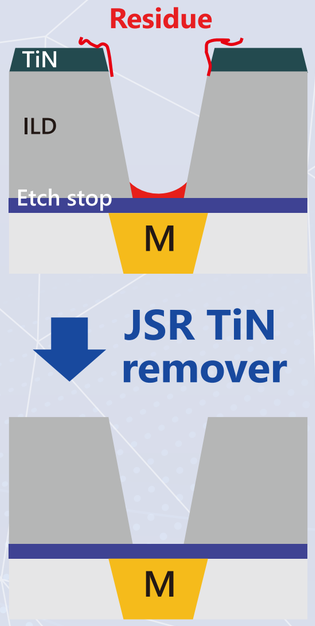


Component		JSR SOG Remover
pH		Alkaline
Etching behavior	SOG	Remove
	SOC	No damage
	ILD	
	SiN	

TiN Remover

TiN hardmask removal Compatible with metals

- ✓ Applicable for TiN remove / pull-back
- ✓ JSR' s metal inhibitors selectively protect each metals



Component		JSR TiN Remover
pH		depends
Etching behavior	PER	Remove
	TiN	
	ILD	No damage
	ES	
	Cu*	
	W*	
	Mo*	

*Cu: Commercially available, W: Sample, Mo: R&D